

REMARKS

Entry of the foregoing amendments, and reexamination and reconsideration of the subject application, and in light of the following remarks, are respectfully requested.

Various claims have been cancelled, and others have been amended, so that all of the claims now consistently recite the as being on the back side of a semiconductor device. None of the cited art shows this structure as originally recited in claim 1, and now present in all of the independent claims.

Takahashi (JP 09-326587) describes a device having a loss material on the wiring surface. The cited English language translation of the specification (¶[0011]), and the drawings (element 2), teach that the high permeability film is in the middle of the device and not on the back surface as presently claimed.

Takahashi does not anticipate the claims.

Inomata discloses a layer in the middle of the active device, like Takahashi, as shown in Figs. 5 and 6 (granular layer 16). Inomata uses the ferromagnetic grains in the layer 16 not for shielding properties but as part of the active component (see third full paragraph in Summary), and so not on the back of the device as presently claimed.

None of the cited art shows or suggests a granular magnetic shielding layer on the back side of a semiconductor device, as specifically claimed, and so the rejections should be withdrawn.